Notification about the transfer of the semiconductor business

The semiconductor business of Panasonic Corporation was transferred on September 1, 2020 to Nuvoton Technology Corporation (hereinafter referred to as "Nuvoton"). Accordingly, Panasonic Semiconductor Solutions Co., Ltd. became under the umbrella of the Nuvoton Group, with the new name of Nuvoton Technology Corporation Japan (hereinafter referred to as "NTCJ").

In accordance with this transfer, semiconductor products will be handled as NTCJ-made products after September 1, 2020. However, such products will be continuously sold through Panasonic Corporation.

Publisher of this Document is NTCJ.

If you would find description "Panasonic" or "Panasonic semiconductor solutions", please replace it with NTCJ.

Except below description page
 "Request for your special attention and precautions in using the technical information and semiconductors described in this book"

Nuvoton Technology Corporation Japan

FC6B22500L

MOS FET

Panasonic

FC6B22500L

Gate resistor installed Dual N-channel MOS FET For lithium-ion secondary battery protection circuits

■ Features

- Source-source On-state Resistance:RSS(on) typ. = $8.3 \text{ m}\Omega$ (VGS = 3.8 V)
- CSP (Chip Size Package)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL : Level 1)
- Marking Symbol: 3S

Packaging

Embossed type (Thermo-compression sealing): 10000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

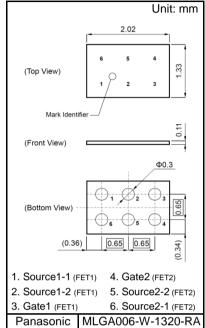
Parameter		Symbol	Rating	Unit
Source-source Voltage		VSS	20	V
Gate-source Voltage	VGS	±12	V	
Source Current	DC *1	IS1	6.2	Α
	DC *2	IS2	11.5	Α
	DC *3	IS3	14.5	Α
	Pulsed *4	ISp	62	Α
Total Power Dissipation	DC *1	PD1	0.44	W
	DC *2	PD2	1.5	W
	DC *3	PD3	2.4	W
Channel Temperature		Tch	150	°C
Storage Temperature Range		Tstg	-55 to +150	°C

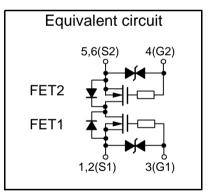
■ Thermal Characteristics

	Rth *1	284	°C/W
Thermal Resistance (ch-a)	Rth *2	83	°C/W
	Rth *3	52	°C / W

Note *1 Mounted on FR4 board ($25.4~\text{mm} \times 25.4~\text{mm} \times t1.0~\text{mm}$). FR4 board partially covered with copper pad ($30~\text{mm}^2$ area, $36~\mu\text{m}$ thickness).

- $^{*}2$ Mounted on FR4 board (25.4 mm \times 25.4 mm \times t1.0 mm). FR4 board fully covered with copper pad (610 mm² area, 35 μm thickness).
- *3 Mounted on Ceramic board ($70 \text{ mm} \times 70 \text{ mm} \times t1.0 \text{ mm}$).
- *4 t = 10 µs, Duty Cycle \leq 1 %





JEITA Code

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Established: 2016-10-07

Revised: 2016-12-07

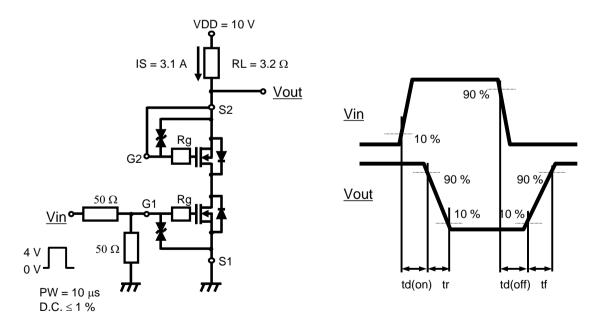
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■ Electrical Characteristics Ta = 25 °C ± 3 °C

	<u> </u>						
Parameter	Symbol	Conditions	Min	Тур	Max	Unit	
Source-source Breakdown Voltage	VSSS	IS = 1 mA, VGS = 0 V	20			V	
Zero Gate Voltage Source Current	ISSS	VSS = 20 V, VGS = 0 V			1.0	μΑ	
Gate-source Leakage Current	IGSS1	$VGS = \pm 8 \text{ V}, VSS = 0 \text{ V}$			±10	μА	
	IGSS2	$VGS = \pm 5 \text{ V}, VSS = 0 \text{ V}$			±1.0		
Gate-source Threshold Voltage	Vth	IS = 0.57 mA, VSS = 10 V	0.35	0.9	1.4	V	
Source-source On-state Resistance	RSS(on)1	IS = 3.1 A, VGS = 4.5 V	5.2	7.9	10.3		
	RSS(on)2	IS = 3.1 A, VGS = 3.8 V	5.5	8.3	10.8	mΩ	
	RSS(on)3	IS = 3.1 A, VGS = 3.1 V	5.8	9.2	14.7		
	RSS(on)4	IS = 3.1 A, VGS = 2.5 V	6.3	11.1	21.8		
Body Diode Forward Voltage	VF(s-s)	IF = 3.1 A, VGS = 0 V		0.7	1.2	V	
Input Capacitance *1	Ciss			1600			
Output Capacitance *1	Coss	VSS = 10 V, VGS = 0 V, f = 1 kHz		165		pF	
Reverse Transfer Capacitance *1	Crss			130			
Turn-on Delay Time *1,*2	td(on)	VDD = 10 V, VGS = 0 to 4.0 V		0.4			
Rise Time *1,*2	tr	IS = 3.1 A		0.9		μS	
Turn-off Delay Time *1,*2	td(off)	VDD = 10 V, VGS = 4.0 to 0 V		2.1			
Fall Time *1,*2	tf	IS = 3.1 A		1.4		μS	
Total Gate Charge *1	Qg	VDD = 10 V		13			
Gate-source Charge *1	Qgs	VGS = 0 to 4.0 V		5.2		nC	
Gate-drain Charge *1	Qgd	IS = 6.2 A		4.0		Ī	

Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

- *1 Guaranteed by design, not subject to production testing.
- *2 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time.



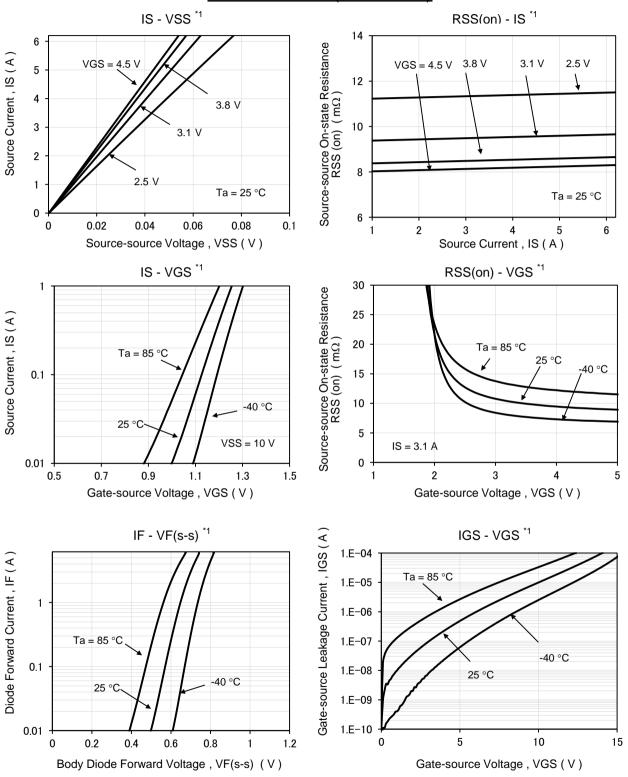
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MOS FET FC6B22500L

Panasonic

Technical Data (reference)



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MOS FET

FC6B22500L

Panasonic

Technical Data (reference) ISS - VSS *1 **Dynamic Input / Output Characteristics** Zero Gate Voltage Source Current , ISS (A) 1.E-04 6 VDD = 10 VGate-source Voltage, VGS (V) 1.E-05 IS = 6.2 A 5 Ta = 25 °C Ta = 85 °C 1.E-06 4 1.E-07 25 °Ç 3 1.E-08 2 1.E-09 1.E-10 -40 °C 1.E-11 10 15 20 30 10 15 20 25 0 Source-source Voltage, VSS (V) Gate Charge, Qg (nC) Safe Operating Area *2 Rth - tsw 1000 Thermal Resistance, Rth (°C/W) Limited by RSS(on) Absolute Maximum Rating *2) GS = 3.8 V100 Source Current, IS (A) 500 μs 100 1 ms 10 3 ms 11 ms 1 100 ms (*3) 10 0.1 DC Ta = 25 °C Ta = 25 °C 0.01 100 0.1 0.001 0.01 0.1 10 100 1000 Source-source Voltage, VSS (V) Pulse Width, tsw(s) Normalized Effective Transient Thermal Impedance Thermal Response *2 10 Note *1 Pulse measurement. Duty Cycle = 0.5 Mounted on FR4 board ($25.4 \text{ mm} \times 25.4 \text{ mm} \times t1.0 \text{ mm}$). FR4 board partially covered with copper pad (30 mm² area, 36 μm thickness). *3 Mounted on FR4 board ($25.4 \text{ mm} \times 25.4 \text{ mm} \times t1.0 \text{ mm}$). 0.1 FR4 board fully covered with copper pad 0.05 (610 mm² area, 35 μm thickness). 0.02 *4 Mounted on Ceramic board ($70 \text{ mm} \times 70 \text{ mm} \times t1.0 \text{ mm}$). 0.01 Single Pulse

Ta = 25 °C

100

1000

10

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0.001

0.001

0.01

0.1

Square Wave Pulse Duration (s)

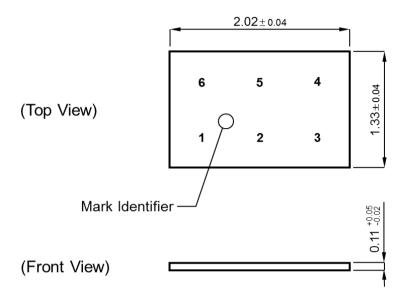
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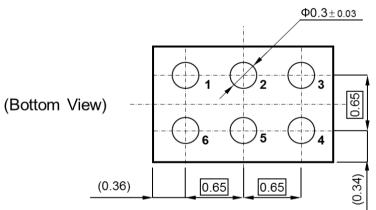
MOS FET

FC6B22500L

■ Outline

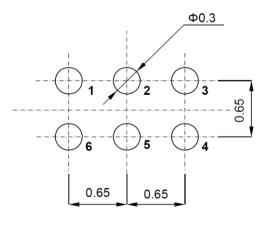
Unit: mm





■ Land & Stencil Pattern (reference)

Unit: mm



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